List of Figures

		Page
Fig. 1-1	The six groups of models proposed to explain luminescence.	6
Fig. .2-1	The profile of TRIM simulation and the secondary ion mass spectrometry (SIMS).	12
Fig. .2-2	The μ-PL spectra of Si-implanted quartz samples at (a) as-implanted condition, or annealed at 1100^{o}C for (b) 1 hr and (c) 3 hrs. The inset figure shows the pure quartz samples (d) before and (e) after annealing at 1100 ^{o}C for 1 hr.	13
Fig. .2-3	The electron paramagnetic resonance (EPR) spectra of the as-implanted and 1-hr annealed Si-implanted quartz.	14
Fig. .2-4	The power dependent μ-PL spectra of the 3-hr annealed Si-implanted quartz at pumping intensity of (a) 10 kW/cm^2, (b) 25 kW/cm^2, (c) 50 kW/cm^2, (d) 100 kW/cm^2, (e) 200 kW/cm^2, (f) 250 kW/cm^2, and (g) 300 kW/cm^2. The inset figure plots the TRIM-simulated and SIMS-measured Si excess density as a function of depth.	16
Fig. .2-5	The wavelength shift of μ-PL for 1-hr and 3-hr annealed Si-implanted quartz samples at different pumping intensity. The inset figure shows the red-shifted μ-PL spectra for the 3-hr annealed sample at pumping intensities of (a) 10 kW/cm^2 and (b) 300 kW/cm^2.	17
Fig. .2-6	(a) n_o and k_o versus wavelength in micrometers for silicon dioxide (type α, crystalline); (b) plot of n_e and k_e versus wavelength in micrometers for silicon dioxide (type β, crystalline).	17
Fig. .2-7	The wavelength depended transmission and absorption curve.	18
Fig. .2-8	The temperature measured setup.	19
Fig. .2-9	The time dependent temperature measured.	19
Fig. .2-10	The accumulated surface charges of (a) 1-hr annealed and (b) 3-hr annealed samples measured before and after illuminating for 12 hours. The inset figure illustrates the red-shifted μ-PL from 3-hr annealed Si-implanted quartz illuminated at 300 kW/cm^2 for 1 hour.	21
Fig. .3-1	The TRIM-simulated Si excess density as a function of depth. The inset figure illustrates the possible photo-electron transport of the SiO_2:Si^+ MSM-PD.	29
Fig. .3-2	(a) The energy–band diagram of the MOS structure. (b) The illustration of Fowler-Nordheim tunneling. (c) The illustration of direct tunneling.	31
Fig. .3-3	The energy-band diagram of forward-biased metal-semiconductor junction.	34
Fig. .3-4	(a) A standard TLM contact-resistance pattern. (b) the expected resistance R as a function id contact-spacing l_i. (c)Two possible scenarios for ohmic metal contacts on the surface of a semiconductor layer. (d) A transmission-line-model equivalent circuit for current flow in a thin-layer semiconductor device.	35
Fig. .3-5	The current-voltage curve for Schottky diodes with 2.5 μm gap spacing made on pure quartz, as-implanted, annealed at 1100^{o}C for 1 hr and 3 hrs.	39
Fig. .3-6	The result of TLM diode of SiO_2:Si^+ as a function of different applied gap spacing.	39

Fig. .3-7	Compared experiment with simulation due to Fowler-Nordheim tunneling, direct tunneling and Schottky barrier model.	41
Fig. .3-8	The current-voltage curve of pure quartz sample for the dark current and the irradiative current.	42
Fig. .3-9	The current-voltage curve of as-implanted sample for the dark current and the irradiative current.	43
Fig. .3-10	The current-voltage curve of 1-hr annealing sample for the dark current and the irradiative current.	43
Fig. .3-11	The current-voltage curve of 3-hr annealing sample for the dark current and the irradiative current.	44
Fig. .3-12	The relationship between photocurrent and bias voltage.	45
Fig. .3-13	The relationship between the responsivity and photocurrent in different condition.	45
Fig. .3-14	The irradiative current of SiO_2:Si^+ with MSM-PD due to different wavelength source.	46
Fig. .3-15	The wavelength dependence of the photocurrent incident power 25 mW for SiO_2:Si^+ MSM-PD.	47